Dual 2-input NAND gate; open drain

Rev. 11 — 8 April 2013

Product data sheet

1. General description

The 74LVC2G38 provides a 2-input NAND function.

The outputs of the 74LVC2G38 devices are open-drain and can be connected to other open-drain outputs to implement active-LOW, wired-OR or active-HIGH wired-AND functions.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant outputs for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - JESD8B/JESD36 (2.7 V to 3.6 V)
- ESD protection:
 - HBM EIA/JESD22-A114F exceeds 2000 V
 - MM EIA/JESD22-A115-A exceeds 200 V
- ± 24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power consumption
- Open-drain outputs
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



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3. Ordering information

Table 1. Ordering information								
Type number	Package							
	Temperature range	Name	Description	Version				
74LVC2G38DP	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2				
74LVC2G38DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1				
74LVC2G38GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 \times 1.95 \times 0.5 mm	SOT833-1				
74LVC2G38GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 \times 1 \times 0.5 mm	SOT1089				
74LVC2G38GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 3 \times 2 \times 0.5 mm	SOT996-2				
74LVC2G38GM	–40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body $1.6 \times 1.6 \times 0.5$ mm	SOT902-2				
74LVC2G38GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.2 \times 1.0 \times 0.35$ mm	SOT1116				
74LVC2G38GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1.0 \times 0.35$ mm	SOT1203				

4. Marking

Table 2.Marking codes

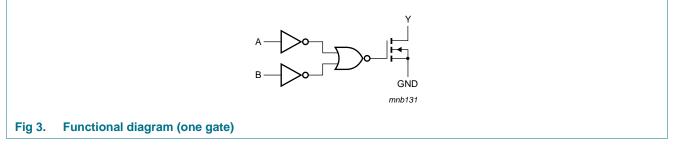
Type number	Marking code ^[1]
74LVC2G38DP	Y38
74LVC2G38DC	Y38
74LVC2G38GT	Y38
74LVC2G38GF	YB
74LVC2G38GD	Y38
74LVC2G38GM	Y38
74LVC2G38GN	YB
74LVC2G38GS	YB

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

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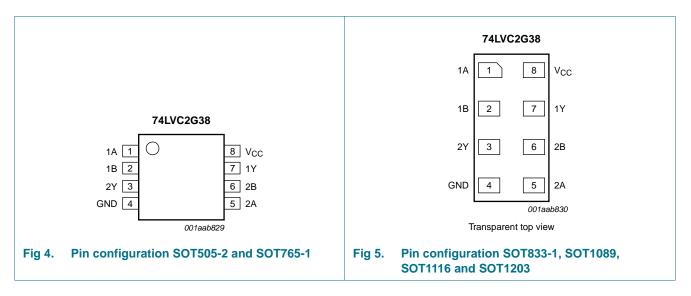
5. Functional diagram



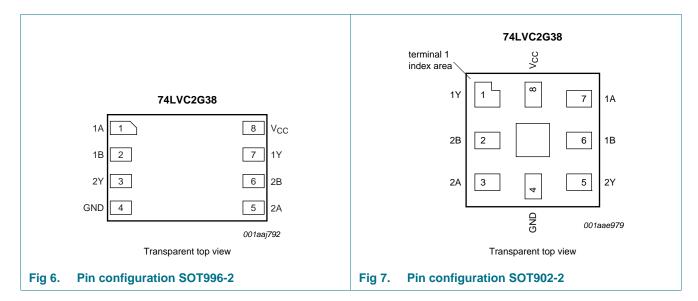


6. Pinning information

6.1 Pinning



Dual 2-input NAND gate; open drain



6.2 Pin description

Symbol	Pin	Description	
	SOT505-2, SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-2	
1A, 2A	1, 5	7, 3	data input
1B, 2B	2, 6	6, 2	data input
GND	4	4	ground (0 V)
1Y, 2Y	7, 3	1, 5	data output
V _{CC}	8	8	supply voltage

7. Functional description

Table 4. Function table^[1]

Input		Output
nA	nB	nY
L	L	Z
L	Н	Z
Н	L	Z
Н	Н	L

[1] H = HIGH voltage level; L = LOW voltage level; Z = high-impedance OFF-state.

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

				.0	,
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
VI	input voltage		<u>[1]</u> –0.5	+6.5	V
Vo	output voltage	Active mode	<u>[1][2]</u> –0.5	+6.5	V
		Power-down mode	<u>[1][2]</u> –0.5	+6.5	V
I _{IK}	input clamping current	V ₁ < 0 V	-50	-	mA
I _{OK}	output clamping current	$V_{\rm O}$ > $V_{\rm CC}$ or $V_{\rm O}$ < 0 V	-	±50	mA
lo	output current	$V_{O} = 0 V$ to V_{CC}	-	±50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T_{amb} = -40 °C to +125 °C	[3] _	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When $V_{CC} = 0 V$ (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.
 For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.
 For XSON8 and XQFN8 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Operating conditions				
Parameter	Conditions	Min	Max	Unit
supply voltage		1.65	5.5	V
input voltage		0	5.5	V
output voltage	Active mode	0	V _{CC}	V
	disable mode	0	5.5	V
	Power-down mode	0	5.5	V
ambient temperature		-40	+125	°C
input transition rise and fall rate	V_{CC} = 1.65 V to 2.7 V	-	20	ns/V
	V_{CC} = 2.7 V to 5.5 V	-	10	ns/V
	Parameter supply voltage input voltage output voltage ambient temperature	Parameter Conditions supply voltage input voltage input voltage Active mode output voltage Active mode disable mode Power-down mode ambient temperature V _{CC} = 1.65 V to 2.7 V	ParameterConditionsMinsupply voltage1.65input voltage0output voltageActive mode0disable mode0Power-down mode0ambient temperature-40input transition rise and fall rate V_{CC} = 1.65 V to 2.7 V-	ParameterConditionsMinMaxsupply voltage1.655.5input voltage05.5output voltageActive mode0 V_{CC} disable mode05.5Power-down mode05.5ambient temperature-40+125input transition rise and fall rate $V_{CC} = 1.65 V$ to 2.7 V-20

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10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

-	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	40 °C to +85 °C[<u>1]</u>					
VIH	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		$V_{CC} = 2.7 V \text{ to } 3.6 V$	2.0	-	-	V
		$V_{CC} = 4.5 V \text{ to } 5.5 V$	$0.7\times V_{CC}$	-	-	V
VIL	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 2.7 V \text{ to } 3.6 V$	-	-	0.8	V
		$V_{CC} = 4.5 V \text{ to } 5.5 V$	-	-	$0.3\times V_{CC}$	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_O = 100 $\mu\text{A};V_{CC}$ = 1.65 V to 5.5 V	-	-	0.1	V
		$I_{O} = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	0.08	0.45	V
		I_{O} = 8 mA; V_{CC} = 2.3 V	-	0.14	0.3	V
		I_0 = 12 mA; V_{CC} = 2.7 V	-	0.19	0.4	V
		$I_{O} = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	0.37	0.55	V
		$I_{O} = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.43	0.55	V
l _l	input leakage current	$V_{\rm I}$ = 5.5 V or GND; $V_{\rm CC}$ = 0 V to 5.5 V	-	±0.1	±5	μΑ
OFF	power-off leakage current	V_{I} or V_{O} = 5.5 V; V_{CC} = 0 V	-	±0.1	±10	μΑ
I _{CC}	supply current	$V_{I} = 5.5 V \text{ or GND};$ $V_{CC} = 1.65 V \text{ to } 5.5 V; I_{O} = 0 A$	-	0.1	10	μA
∆l _{CC}	additional supply current	per pin; V _I = V _{CC} – 0.6 V; I _O = 0 A; V _{CC} = 2.3 V to 5.5 V	-	5	500	μA
Cı	input capacitance		-	2.5	-	pF
T _{amb} = -	40 °C to +125 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
		$V_{CC} = 4.5 \text{ V} \text{ to } 5.5 \text{ V}$	$0.7\times V_{CC}$	-	-	V
VIL	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	-	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V	-	-	$0.3\times V_{CC}$	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_O = 100 μ A; V_{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		$I_0 = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.70	V
		$I_0 = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_0 = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.60	V
		$I_0 = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.80	V
		I_{O} = 32 mA; V_{CC} = 4.5 V	-	-	0.80	V
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Product d	ata shoot	Rev. 11 — 8 April 2013				6 (

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At recommended operating conditions; voltages are referenced to GND (ground = 0 V).						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
l _l	input leakage current	$V_{\rm I}$ = 5.5 V or GND; $V_{\rm CC}$ = 0 V to 5.5 V	-	-	±20	μΑ
I _{OFF}	power-off leakage current	$V_{I} \text{ or } V_{O} = 5.5 \text{ V}; V_{CC} = 0 \text{ V}$	-	-	±20	μA
I _{CC}	supply current	$V_{I} = 5.5 V \text{ or GND};$ $V_{CC} = 1.65 V \text{ to } 5.5 V; I_{O} = 0 \text{ A}$	-	-	40	μΑ
ΔI_{CC}	additional supply current	per pin; V _I = V _{CC} – 0.6 V; I _O = 0 A; V _{CC} = 2.3 V to 5.5 V	-	-	5000	μΑ

Table 7. Static characteristics ...continued

[1] All typical values are measured at T_{amb} = 25 °C.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		–40 °C to +85 °C			–40 °C to +125 °C		Unit
				Min	Typ <mark>[1]</mark>	Max	Min	Max	
t _{PZL}	OFF-state to LOW	nA, nB to nY; see Figure 8							
	propagation delay	V_{CC} = 1.65 V to 1.95 V		1.2	3.0	8.6	1.2	10.8	ns
		V_{CC} = 2.3 V to 2.7 V		0.7	1.8	4.8	0.7	6.0	ns
		$V_{CC} = 2.7 V$		0.7	2.5	4.4	0.7	5.5	ns
		V_{CC} = 3.0 V to 3.6 V		0.7	2.1	4.1	0.7	5.2	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	1.5	3.3	0.5	4.2	ns
t _{PLZ}	LOW to OFF-state	nA, nB to nY; see Figure 8							
	propagation delay	V_{CC} = 1.65 V to 1.95 V		1.2	3.0	8.6	1.2	10.8	ns
		V_{CC} = 2.3 V to 2.7 V		0.7	1.8	4.8	0.7	6.0	ns
		$V_{CC} = 2.7 V$		0.7	2.5	4.4	0.7	5.5	ns
		V_{CC} = 3.0 V to 3.6 V		0.7	2.1	4.1	0.7	5.2	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	1.5	3.3	0.5	4.2	ns
C _{PD}	power dissipation capacitance	per gate; V_I = GND to V_{CC}	[2]	-	5	-	-	-	pF

[1] Typical values are measured at nominal V_{CC} and at T_{amb} = 25 °C.

 $[2] \quad C_{PD} \text{ is used to determine the dynamic power dissipation } (P_D \text{ in } \mu W). \\ P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o) \text{ where:}$

 $f_i = input frequency in MHz;$

 $f_o =$ output frequency in MHz;

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$ = sum of outputs.

Dual 2-input NAND gate; open drain

12. Waveforms

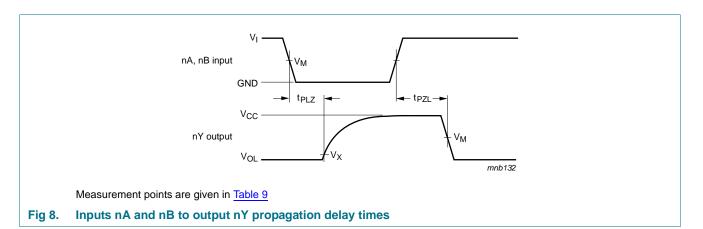


Table 9.Measurement points

Supply voltage	Input	Output	
V _{cc}	V _M	V _X	V _M
1.65 V to 1.95 V	$0.5 imes V_{CC}$	V _{OL} + 0.15 V	$0.5\times V_{CC}$
2.3 V to 2.7 V	$0.5 imes V_{CC}$	V _{OL} + 0.15 V	$0.5 imes V_{CC}$
2.7 V	1.5 V	V _{OL} + 0.3 V	1.5 V
3.0 V to 3.6 V	1.5 V	V _{OL} + 0.3 V	1.5 V
4.5 V to 5.5 V	$0.5 imes V_{CC}$	V _{OL} + 0.3 V	$0.5 imes V_{CC}$

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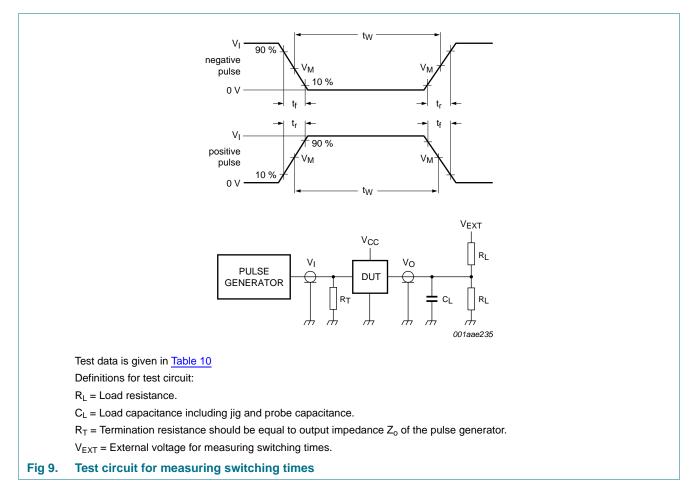


Table 10. Test data

Supply voltage	Input		Load		V _{EXT}
V _{cc}	VI	t _r , t _f	CL	RL	t _{PLZ} , t _{PZL}
1.65 V to 1.95 V	V _{CC}	\leq 2.0 ns	30 pF	1 kΩ	$2 \times V_{CC}$
2.3 V to 2.7 V	V _{CC}	\leq 2.0 ns	30 pF	500 Ω	$2 \times V_{CC}$
2.7 V	2.7 V	\leq 2.5 ns	50 pF	500 Ω	6 V
3.0 V to 3.6 V	2.7 V	\leq 2.5 ns	50 pF	500 Ω	6 V
4.5 V to 5.5 V	V _{CC}	\leq 2.5 ns	50 pF	500 Ω	$2\times V_{CC}$

Dual 2-input NAND gate; open drain

13. Package outline

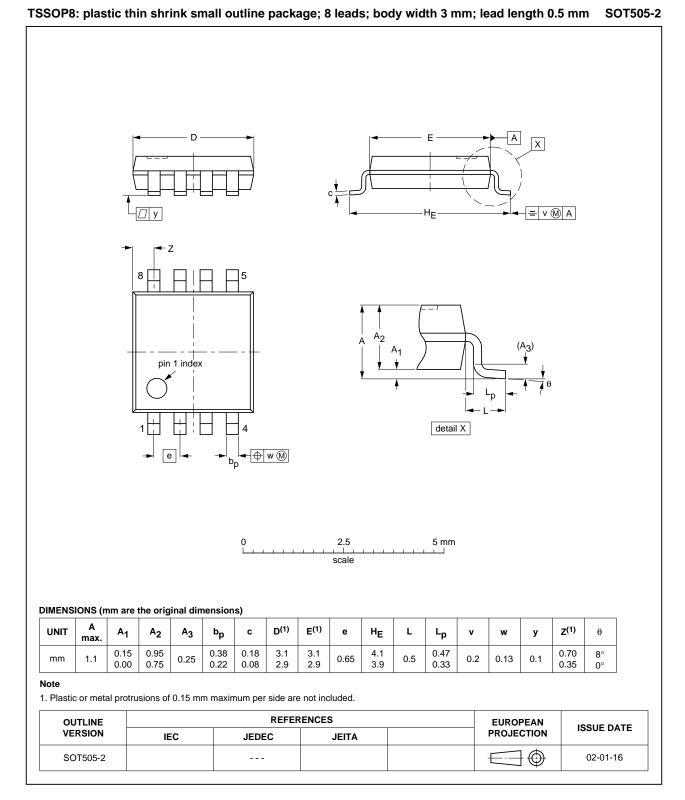


Fig 10. Package outline SOT505-2 (TSSOP8)

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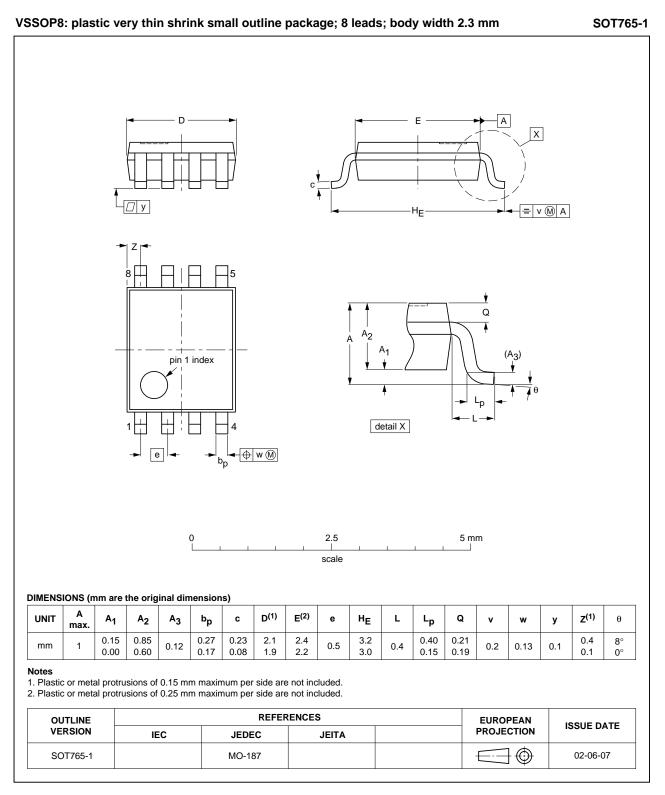


Fig 11. Package outline SOT765-1 (VSSOP8)

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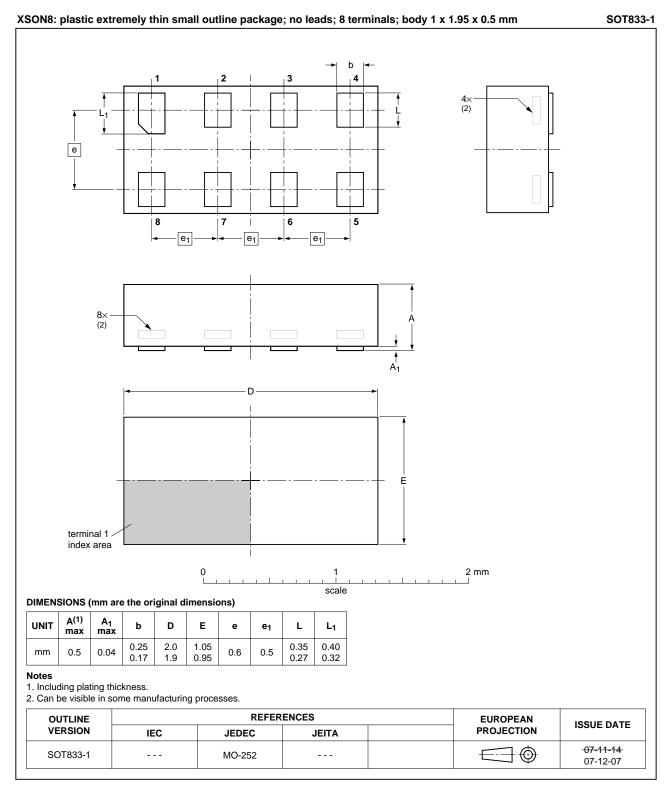
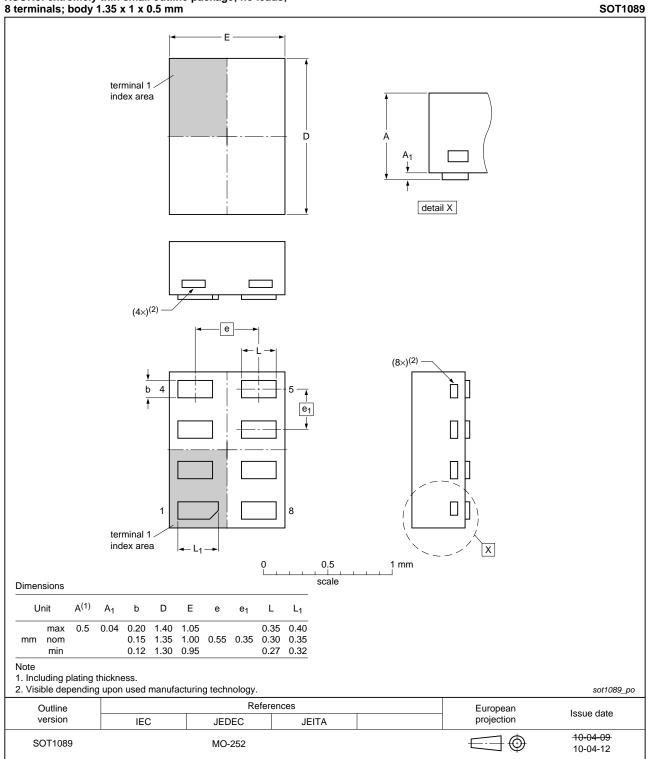


Fig 12. Package outline SOT833-1 (XSON8)

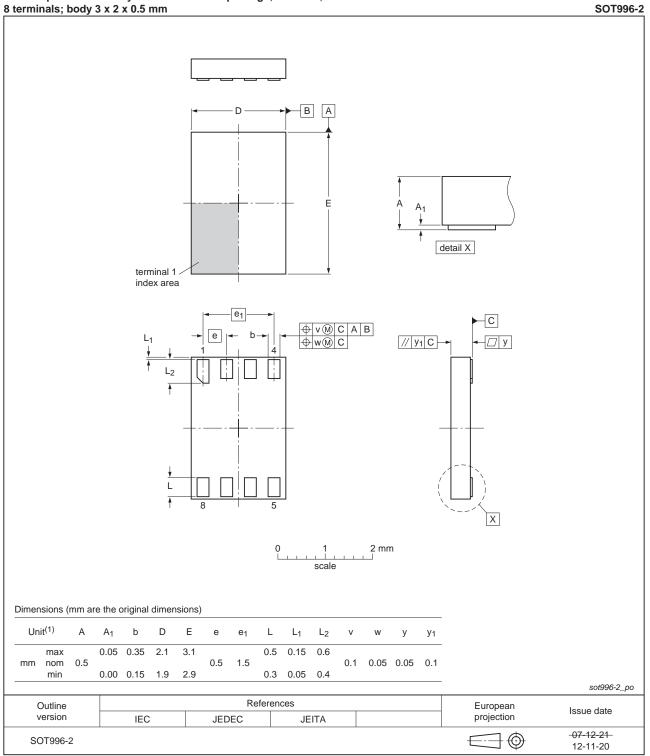
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XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1 x 0.5 mm

Fig 13. Package outline SOT1089 (XSON8)

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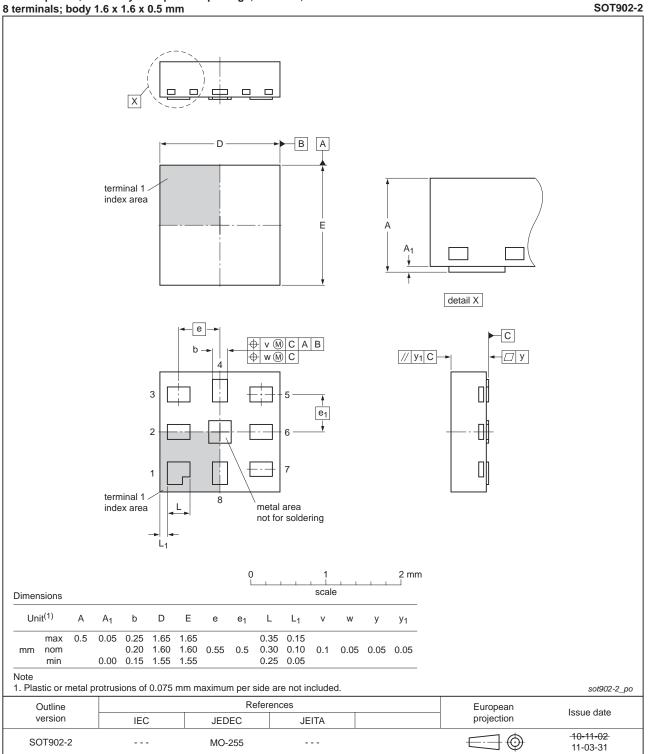


XSON8: plastic extremely thin small outline package; no leads; 8 terminals: body 3 x 2 x 0.5 mm

Fig 14. Package outline SOT996-2 (XSON8)

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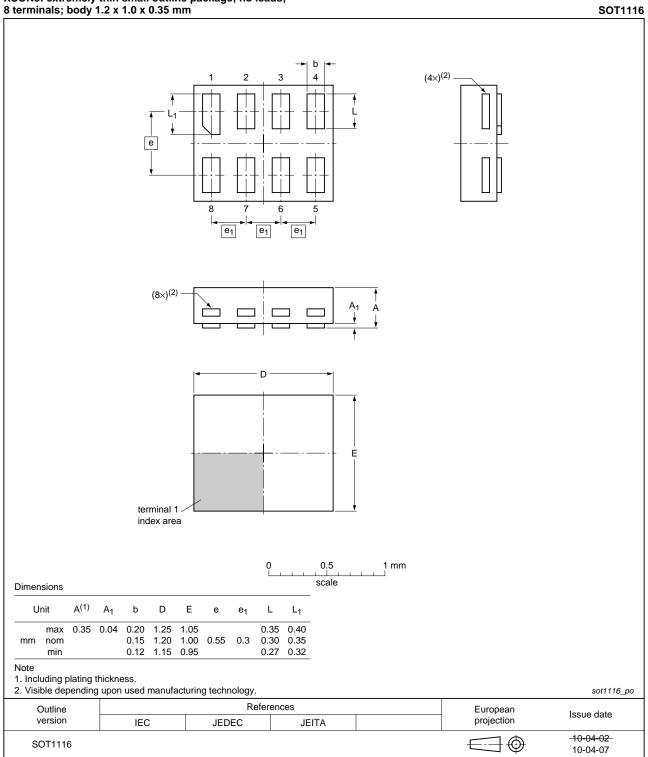


XQFN8: plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 x 1.6 x 0.5 mm

Fig 15. Package outline SOT902-2 (XQFN8)

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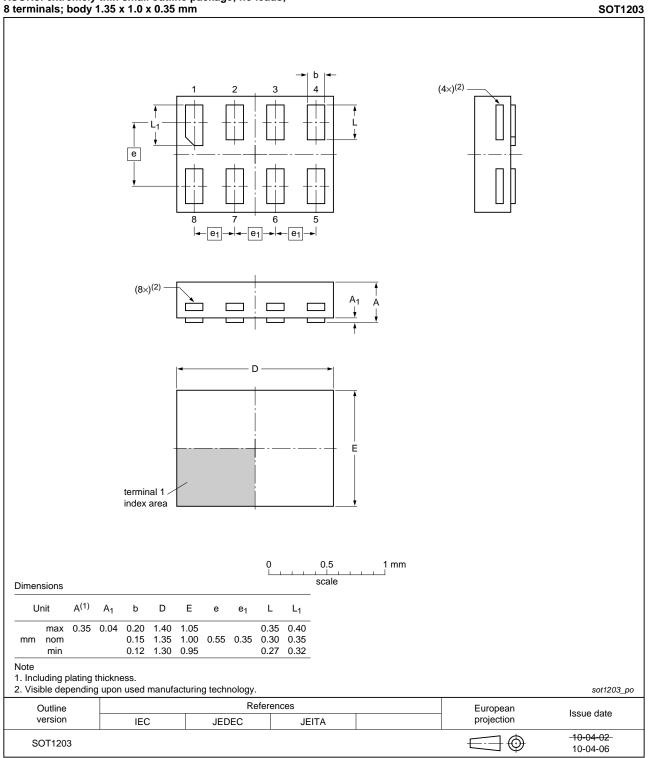


XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.2 x 1.0 x 0.35 mm

Fig 16. Package outline SOT1116 (XSON8)

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XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1.0 x 0.35 mm

Fig 17. Package outline SOT1203 (XSON8)

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14. Abbreviations

Table 11. Abbre	eviations
Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. **Revision history Document ID Release date** Data sheet status **Change notice Supersedes** 74LVC2G38 v.11 20130408 Product data sheet 74LVC2G38 v.10 -Modifications: For type number 74LVC2G38GD XSON8U has changed to XSON8. 74LVC2G38 v.10 Product data sheet 74LVC2G38 v.9 20120628 Modifications: For type number 74LVC2G38GM the SOT code has changed to SOT902-2. 74LVC2G38 v.9 20111128 Product data sheet 74LVC2G38 v.8 -Modifications: • Legal pages updated. 74LVC2G38 v.8 20101104 Product data sheet 74LVC2G38 v.7 _ 74LVC2G38 v.7 20090320 Product data sheet 74LVC2G38 v.6 -Product data sheet 74LVC2G38 v.6 20080219 74LVC2G38 v.5 _ 74LVC2G38 v.5 20070904 Product data sheet 74LVC2G38 v.4 -74LVC2G38 v.4 20060516 Product data sheet 74LVC2G38 v.3 -74LVC2G38 v.3 20050201 Product specification 74LVC2G38 v.2 -74LVC2G38 v.2 20041018 Product specification 74LVC2G38 v.1 -74LVC2G38 v.1 20031027 Product specification -_

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16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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